IN THE CLAIMS

Please amend the claims as follows.

For the Examiner's convenience, a list of all claims is included below.

- 1-11 (Cancelled)
- 12. (Currently Amended) A process comprising:

forming a metallization over a substrate;

forming a metal adhesion first layer above and on the metallization;

forming a metal second layer above and on the metal adhesion first layer

forming a metal third layer above and on the metal second layer;

forming a solder bump above and on the metal third layer, and

wherein at least one of the metal second layer comprises a copper and the

metal third layer comprises sputtered copper is selected from a group consisting of

a refractory metal, a metal-doped refractory metal, and a refractory metal alloy.

13. (Original) The process according to claim 12, forming a metal adhesion first layer further comprising:

sputtering a composition over the metallization under conditions to impart a compressive stress in the metal adhesion first layer, wherein the composition is selected from Ti, TiW, W and Cr.

14. (Currently Amended) A process comprising:

forming a metallization over a substrate;

forming a metal adhesion first layer above and on the metallization;

sputtering a copper metal second layer above and on the metal adhesion first layer under conditions to impart a compressive stress therein;

forming a metal third layer above and on the copper metal second layer under conditions to impart a compressive stress therein, wherein the metal third layer is selected from a group consisting of a refractory metal, a metal-doped refractory metal, and a refractory metal alloy;

forming a solder bump above and on the metal third layer The process to claim 12, forming the metal second layer

under conditions to impart a compressive stress therein; and forming the metal third layer further comprising:—sputtering the metal third layer under conditions to impart a compressive stress therein, wherein the metal third layer is selected from a refractory metal, a metal doped refractory metal, or a refractory metal alloy.

15-16 (Cancelled)

- 17. (Original) The process according to claim 12, further comprising:

 forming an electrically conductive bump above and on the metal third layer.
- 18. (Currently Amended) A process comprising:
 forming a copper pad over a metal-sex (M6) metallization substrate;

sputtering a Ti metal adhesion first layer above and on the metallization copper pad;

sputtering a metal second layer above and on the Ti metal adhesion first layer;

forming a metal third layer above and on the metal second layer;

forming a solder bump above and on the metal third layer, and

wherein at least on of the metal second layer comprises copper and the

metal third layer comprises copper is selected from a group consisting of a

refractory metal, a metal-doped refractory metal, and a refractory metal alloy.

19. (Currently Amended) The process according to claim 18, wherein sputtering a Ti metal adhesion first layer above and on the metallization copper pad comprises:

sputtering a Ti composition over the metallization, wherein the Ti composition has a thickness in a range from about 500 Å to about 4,000 Å.

- 20. (Cancelled)
- 21. (Currently Amended) A process comprising:

 forming a copper pad over a substrate;

 sputtering a Ti metal adhesion first layer above and on the copper pad;

 sputtering a metal second layer above and on the Ti metal adhesion first layer;

forming a metal third layer above and on the metal second layer;

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forming a solder bump above and on the metal third layer,

The process according to claim 18, wherein forming a the metal third layer

comprises:

sputtering a NiV composition over the metal second layer, wherein the NiV composition has a thickness in a range from 1,000 Å to about 5,000 Å, and wherein the metal second layer has a thickness in a range from about 1,000 Å to about 5,000 Å.

22-28 (Cancelled)